L Number	Hits	Search Text	DB	Time stamp
1	39	(electrode$1 conduct$3) near2 (free$2 random$2) near2 (arrang$3 mov$6) near2 (insulat$3 dielectric substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 09:54
2	332	(phase near change) with (Ge near Sb near Te)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 09:54
3	46	((phase near change) with (Ge near Sb near Te)) and (electrode conduct$3) with (Rh Pt Pd Ni Co Cr Re Ir Au)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:16
4	30	(((phase near change) with (Ge near Sb near Te)) and (electrode conduct$3) with (Rh Pt Pd Ni Co Cr Re Ir Au)) and (polycarbonate near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17
5	166992	(electrode conduct$3 contact) with (Rh Pt Pd Ni Co Cr Re Ir Au)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17
6	54	((electrode conduct$3 contact) with (Rh Pt Pd Ni Co Cr Re Ir Au)) and ((phase near change) with (Ge near Sb near Te))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17
7	33	(((electrode conduct$3 contact) with (Rh Pt Pd Ni Co Cr Re Ir Au)) and ((phase near change) with (Ge near Sb near Te))) and (polycarbonate near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 10:17

L Number	Hits	Search Text	DB	Time stamp
1	3089644	non nearvolatile near memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:29
2	57541	non near volatile near memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:30
3	6674	cell$1 with different with (electrode$1 conductor$1 contact$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:37
4	14	(cell$1 with different with (electrode$1 conductor$1 contact$1)) and (phase near charge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:34
5	99	(cell$1 with different with (electrode$1 conductor$1 contact$1)) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:50
6	273	(cell$1 with different with (electrode$1 conductor$1 contact$1)) and (non near volatile near memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:50
7	2	((cell$1 with different with (electrode$1 conductor$1 contact$1)) and (non near volatile near memory)) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:37
8	3	cell$1 with different with (electrode$1 conductor$1 contact$1) with (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:53
9	0	(memory near cell$1) with different with (electrode$1 conductor$1 contact$1) with (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:54
10	13	(memory near cell$1) same different same (electrode$1 conductor$1 contact$1) same (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 14:57
11	15	electrode$1 with (randomly near (arrang$3 configur$3)) with (insulat$3 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:13
12	41	electrode$1 with (randomly near (arrang$3 configur$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:21

13	41	electrode$1 with (randomly near (arrang$10 configur$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:22
14	57	(non near volatile near memory) and (randomly near (arrang$10 configur$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:28
15	41	(advantage benifit$1) with (randomly near (arrang$10 configur$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:35
16	443	(advantage benifit$1) with random$4 with (arrang$10 configur$10)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:36
17	43	(advantage benefit$1) with (randomly near (arrang$10 configur$10))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:35
18	469	(advantage benefit$1) with random$4 with (arrang$10 configur$10)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 15:36
20	2	(((advantage benefit$1) with random$4 with (arrang$10 configur$10)) and (electrode$1 conductor$1 contact$1)) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:40
19	164	((advantage benefit$1) with random$4 with (arrang$10 configur$10)) and (electrode$1 conductor$1 contact$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:21
21	66	(electrode$1 conductor$1 contact$1) near2 diameter near2 nm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:35
22	6	(electrode$1 conductor$1) near2 diameter near2 ((5.0 near nm) ("500" near nm))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:40
23	22777	(electrode$1 conductor$1) near2 diameter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:40
24	357	((electrode$1 conductor$1) near2 diameter) and (phase near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 16:41

| 25 | 51 | (((electrode$1 conductor$1) near2 diameter) and (phase near change)) and (non near volatile near memory) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/12 16:41 |